

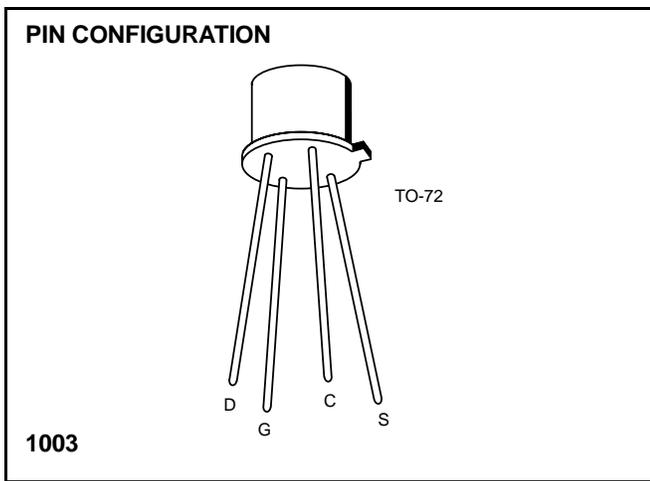
N-Channel Enhancement Mode MOSFET General Purpose Amplifier Switch



IT1750

FEATURES

- Low ON Resistance
- Low C_{dg}
- High Gain
- Low Threshold Voltage



ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise specified)

Drain-Source and Gate-Source Voltage	25V
Peak Gate-Source Voltage (Note 1)	$\pm 125\text{V}$
Drain Current	100mA
Storage Temperature Range	-65°C to $+200^\circ\text{C}$
Operating Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10sec)	$+300^\circ\text{C}$
Power Dissipation	375mW
Derate above 25°C	3mW/ $^\circ\text{C}$

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
IT1750	Hermetic TO-72	-55°C to $+150^\circ\text{C}$
XIT1750	Sorted Chips in Carriers	-55°C to $+150^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Body connected to Source and $V_{BS} = 0$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
$V_{GS(th)}$	Gate to Source Threshold Voltage	0.50	3.0	V	$V_{DS} = V_{GS}$, $I_D = 10\mu\text{A}$
I_{DSS}	Drain Leakage Current		10	nA	$V_{DS} = 10\text{V}$, $V_{GS} = 0$
I_{GSS}	Gate Leakage Current	(See note 2)			
BV_{DSS}	Drain Breakdown Voltage	25		V	$I_D = 10\mu\text{A}$, $V_{GS} = 0$
$r_{DS(on)}$	Drain to Source on Resistance		50	ohms	$V_{GS} = 20\text{V}$
$I_{D(on)}$	Drain Current	10		mA	$V_{DS} = V_{GS} = 10\text{V}$
Y_{fs}	Forward Transadmittance	3,000		μS	$V_{DS} = 10\text{V}$, $I_D = 10\text{mA}$, $f = 1\text{kHz}$
C_{iss}	Total Gate Input Capacitance		6.0	pF	$I_D = 10\text{mA}$, $V_{DS} = 10\text{V}$, $f = 1\text{MHz}$ (Note 3)
C_{dg}	Gate to Drain Capacitance		1.6	pF	$V_{DG} = 10\text{V}$, $f = 1\text{MHz}$ (Note 3)

- NOTES:**
1. Devices must not be tested at $\pm 125\text{V}$ more than once nor longer than 300ms.
 2. Actual gate current is immeasurable. Package suppliers are required to guarantee a package leakage of $< 10\text{pA}$. External package leakage is the dominant mode which is sensitive to both transient and storage environment, which cannot be guaranteed.
 3. For design reference only, not 100% tested.